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Hyperfast Rectifier, 75 A FRED Pt[®] G5



PRIMARY CHARACTERISTICS					
I _{F(AV)}	75 A				
V _R	600 V				
V _F at I _F at 125 °C	1.4 V				
t _{rr} (typ.)	29				
I _{FSM}	565				
T _J max.	175 °C				
Package	TO-247AD 2L				
Circuit configuration	Single				

LINKS TO ADDITIONAL RESOURCES



FEATURES

- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature FREE
- · Polyimide passivation
- AEC-Q101 qualified meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV on-board battery chargers

MECHANICAL DATA

Case: TO-247AD 2L

Molding compound meets UL 94 V-0 flammability rating **Terminal:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	V _{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 103 °C, D = 0.50	75				
Non-repetitive peak surge current	I _{FSM}	T_{C} = 25 °C, t_{p} = 10 ms, sine wave	565	A			
Repetitive peak forward current	I _{FRM}	T _C = 103 °C, D = 0.50, f = 20 kHz	150				
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-		
Forward voltage	VF	I _F = 75 A	-	1.6	2.2	V	
Forward voltage	۷F	I _F = 75 A, T _J = 125 °C	-	1.4	-		
Reverse leakage current	I	$V_{R} = V_{R}$ rated	-	-	25		
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA	
Junction capacitance	CT	V _R = 200 V	-	96	-	pF	
Series inductance	Ls	Measured to lead 5 mm from package body	-	8	-	nH	

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Pb-free RoHS

COMPLIANT

HALOGEN

VS-E5PX7506LHN3



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100$) A/µs, V _R = 30 V	-	29	-	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	44	-	ns
		T _J = 125 °C		-	69	-	
Peok recovery ourrent		T _J = 25 °C	$I_F = 50 A$	-	18	-	A
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 1000 A/μs V _R = 400 V	-	42	-	
	0	T _J = 25 °C		-	484	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1731	-	
	1	T _J = 25 °C	I _F = 75 A dI _F /dt = 1000 A/μs V _B = 400 V	-	48	-	ns
Reverse recovery time	t _{rr}	T _J = 125 °C		-	75	-	
Deck recovery convert		T _J = 25 °C		-	21	-	A
Peak recovery current	I _{RRM}	T _J = 125 °C		-	46	-	
D		T _J = 25 °C		-	573	-	
Reverse recovery charge Q _{rr}		T _J = 125 °C]	-	2048	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R _{thJC}		-	-	0.5	°C/W
Woight			-	5.5	-	g
Weight			-	0.2	-	oz.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Marking device		Case style: TO-247AD 2L	E5PX7506LH			

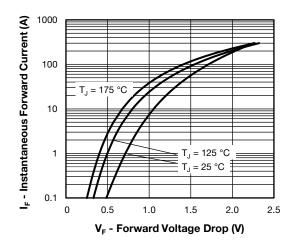


Fig. 1 - Forward Voltage Drop Characteristics

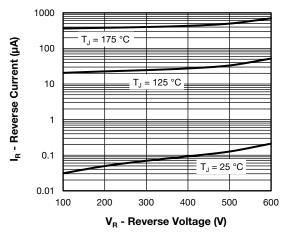


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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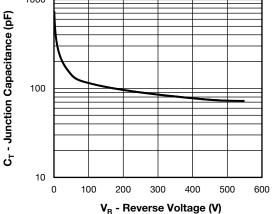


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

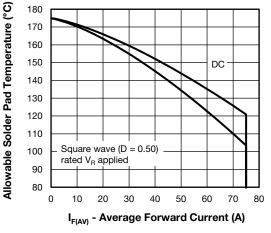


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

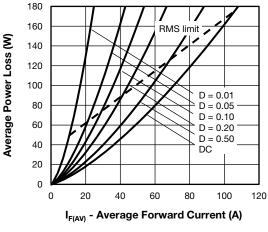


Fig. 5 - Forward Power Loss Characteristics

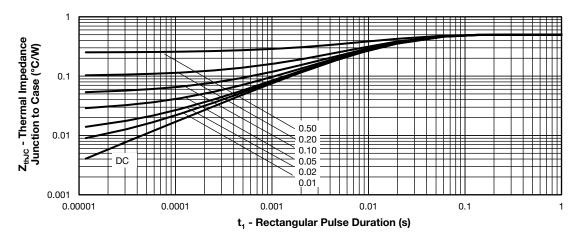


Fig. 6 - Transient Thermal Impedance, Junction to Case

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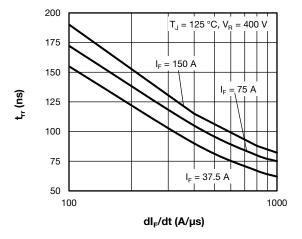


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

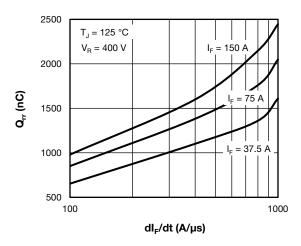


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt

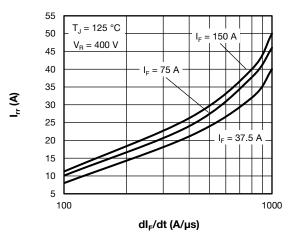


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

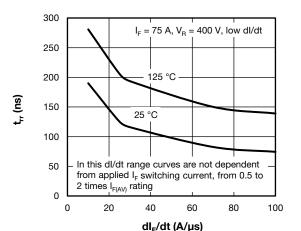
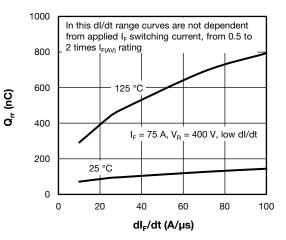


Fig. 10 - Typical Reverse Recovery Time vs. dl_F/dt





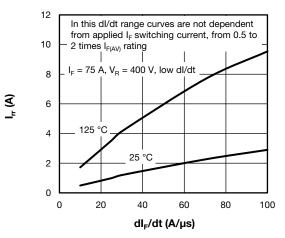


Fig. 12 - Typical Reverse Recovery Current vs. dl_F/dt

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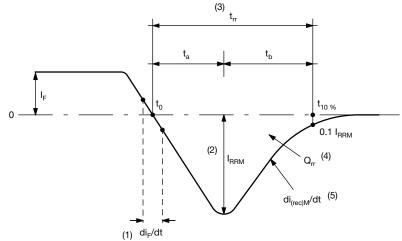


Fig. 13 - Reverse Recovery Waveform and Definitions

Notes

 $^{(1)}~di_{F}/dt$ - rate of change of current through zero crossing

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- ⁽²⁾ I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~~Q_{rr}$ area under curve defined by t_0 and $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code	VS-	Е	5	Р	x	75	06	L	н	N3
	1	2	3	4	5	6	7	8	9	10
	1 - 2 - 3 - 3 - 4 - 5 - 6 - 7 - 8 - 9 -	 Circ E = FRE P = Pro X = Cur Volt Pac 	2 (3) (4) (5) (6) (7) (8) (9) (10) Vishay Semiconductors product Circuit configuration E = single diode FRED Pt [®] Gen 5 P = TO-247 package Process type: X = hyperfast recovery Current rating (75 = 75 A) Voltage rating (06 = 600 V) Package: L = long lead (TO-247AD) H = AEC-Q101 qualified							
	10 -)-free	

ORDERING INFORMATION (Example)								
PREFERRED P/N	RED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-E5PX7506LHN3	25	500	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95536
Part marking information	www.vishay.com/doc?95648

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